

P-Channel 12-V (D-S) MOSFET

PRODUCT SUMMARY		
V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A)
- 12	0.0085 at $V_{GS} = - 4.5$ V	- 9.5
	0.0106 at $V_{GS} = - 2.5$ V	- 8.5
	0.014 at $V_{GS} = - 1.8$ V	- 7.5

FEATURES

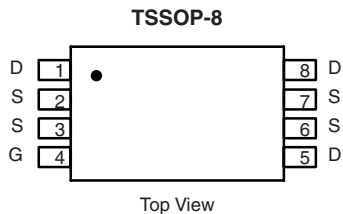
- Halogen-free
- TrenchFET[®] Power MOSFET



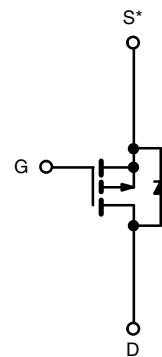
RoHS
COMPLIANT

APPLICATIONS

- Load Switch



Ordering Information: Si6423DQ-T1-GE3 (Lead (Pb)-free and Halogen-free)



* Source Pins 2, 3, 6 and 7 must be tied common.

P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS $T_A = 25$ °C, unless otherwise noted					
Parameter	Symbol	10 s	Steady State	Unit	
Drain-Source Voltage	V_{DS}	- 12		V	
Gate-Source Voltage	V_{GS}	± 8			
Continuous Drain Current ($T_J = 150$ °C) ^a	I_D	$T_A = 25$ °C	- 9.5	- 8.2	A
		$T_A = 70$ °C	- 8	- 6.5	
Pulsed Drain Current (10 μ s Pulse Width)	I_{DM}	- 30			
Continuous Source Current (Diode Conduction) ^a	I_S	- 1.35	- 0.95		
Maximum Power Dissipation ^a	P_D	$T_A = 25$ °C	1.5	1.05	W
		$T_A = 70$ °C	1.0	0.67	
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to 150		°C	

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^a	$t \leq 10$ s	R_{thJA}	60	83	°C/W
	Steady State		100	120	
Maximum Junction-to-Foot	Steady State	R_{thJF}	35	45	

Notes:

a. Surface Mounted on 1" x 1" FR4 board.

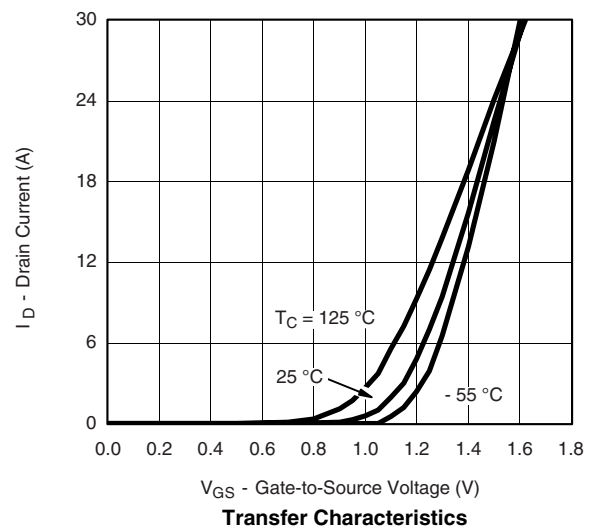
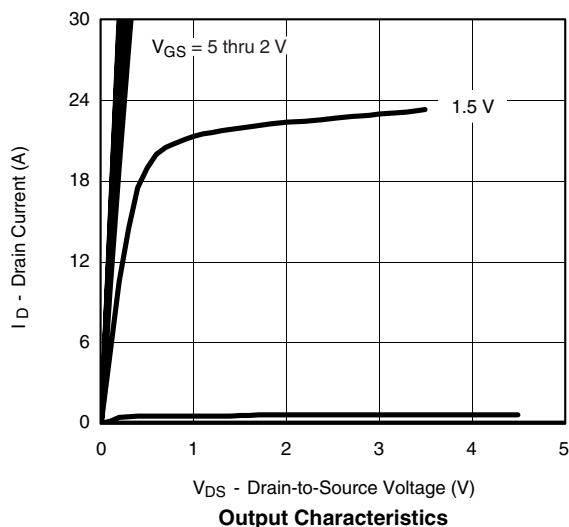
SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -400\text{ }\mu\text{A}$	-0.40		-0.8	V
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 8\text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -12\text{ V}, V_{GS} = 0\text{ V}$			-1	μA
		$V_{DS} = -12\text{ V}, V_{GS} = 0\text{ V}, T_J = 70\text{ }^\circ\text{C}$			-10	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} = -5\text{ V}, V_{GS} = -4.5\text{ V}$	-20			A
Drain-Source On-State Resistance ^a	$R_{DS(on)}$	$V_{GS} = -4.5\text{ V}, I_D = -9.5\text{ A}$		0.0068	0.0085	Ω
		$V_{GS} = -2.5\text{ V}, I_D = -8.5\text{ A}$		0.0085	0.0106	
		$V_{GS} = -1.8\text{ V}, I_D = -7.5\text{ A}$		0.0112	0.014	
Forward Transconductance ^a	g_{fs}	$V_{DS} = -15\text{ V}, I_D = -9.5\text{ A}$		45		S
Diode Forward Voltage ^a	V_{SD}	$I_S = -1.3\text{ A}, V_{GS} = 0\text{ V}$		-0.58	-1.1	V
Dynamic^b						
Total Gate Charge	Q_g	$V_{DS} = -6\text{ V}, V_{GS} = -5\text{ V}, I_D = -9.5\text{ A}$		74	110	nC
Gate-Source Charge	Q_{gs}			9.0		
Gate-Drain Charge	Q_{gd}			19		
Gate Resistance	R_g			3.6		Ω
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -6\text{ V}, R_L = 6\text{ }\Omega$ $I_D = -1\text{ A}, V_{GEN} = -4.5\text{ V}, R_G = 6\text{ }\Omega$		50	75	ns
Rise Time	t_r			75	110	
Turn-Off Delay Time	$t_{d(off)}$			270	400	
Fall Time	t_f			200	300	
Source-Drain Reverse Recovery Time	t_{rr}	$I_F = -1.3\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$		160	250	

Notes:

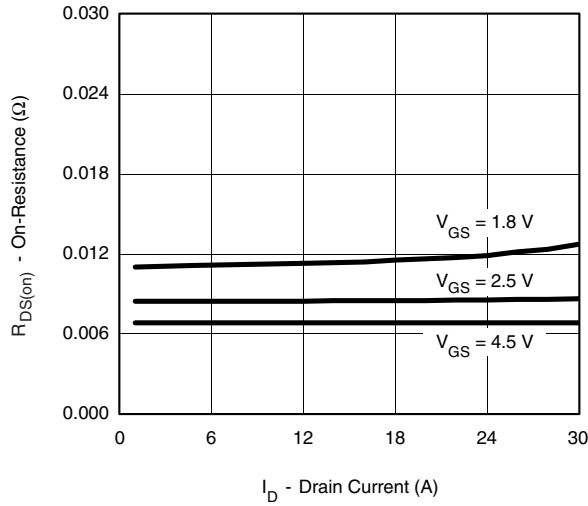
- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
 b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

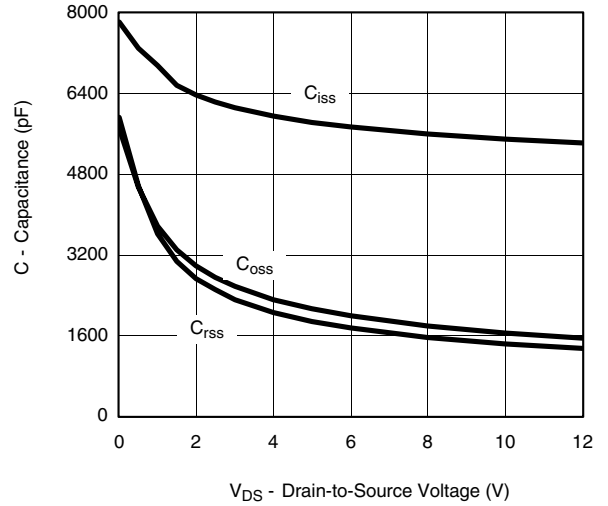
TYPICAL CHARACTERISTICS $25\text{ }^\circ\text{C}$, unless otherwise noted



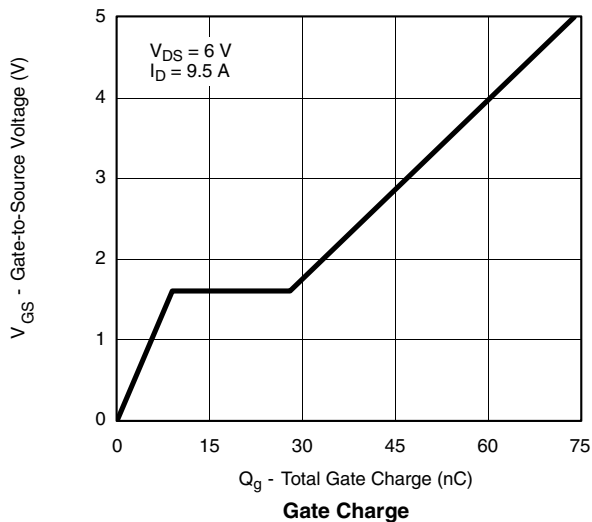
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



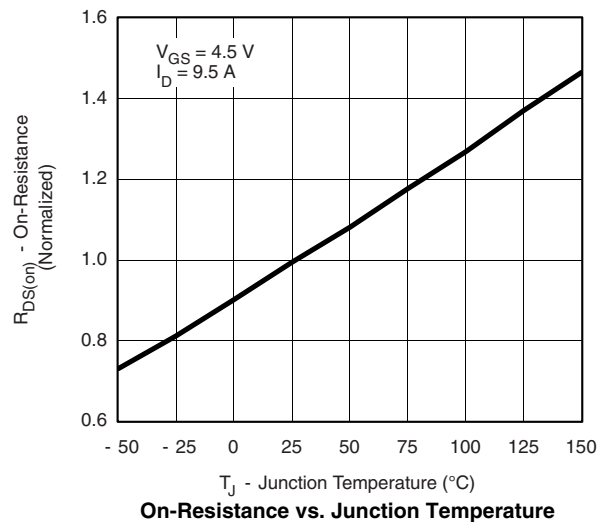
On-Resistance vs. Drain Current



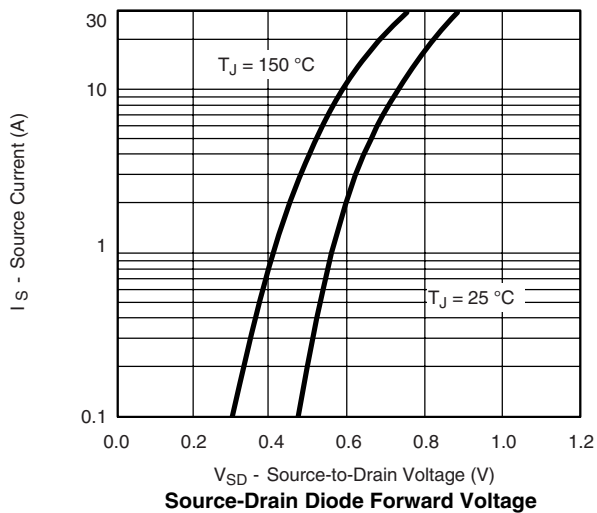
Capacitance



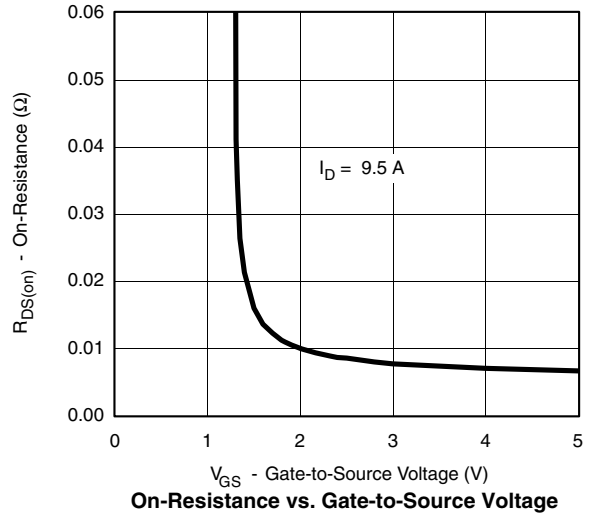
Gate Charge



On-Resistance vs. Junction Temperature

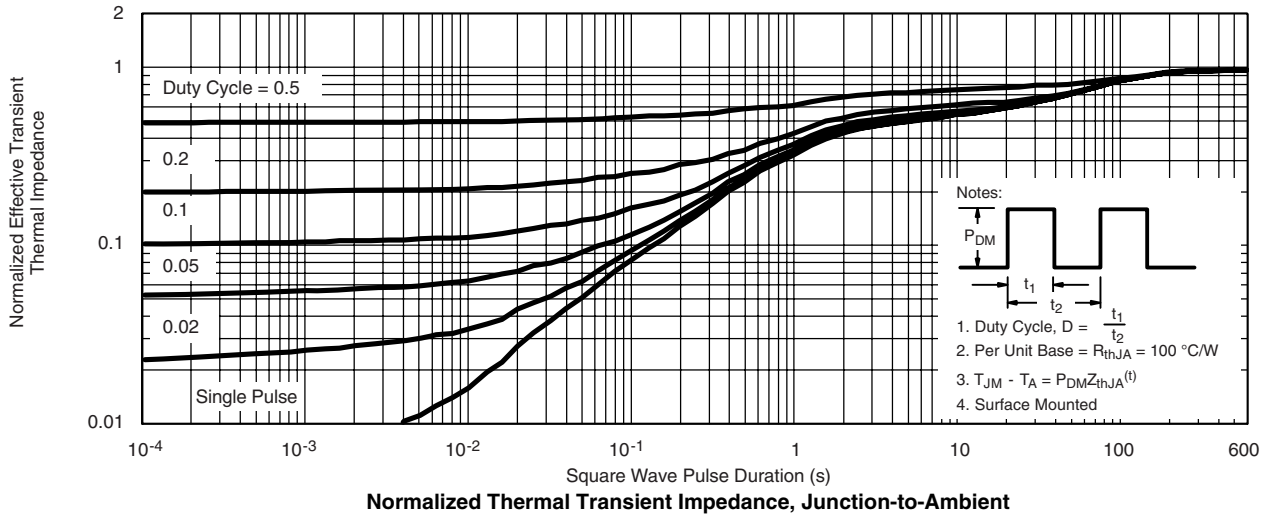
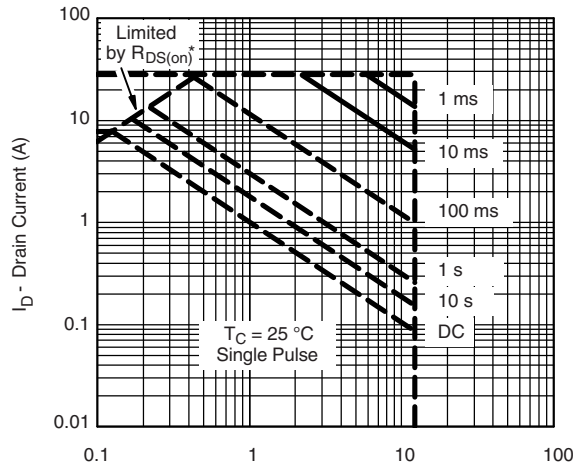
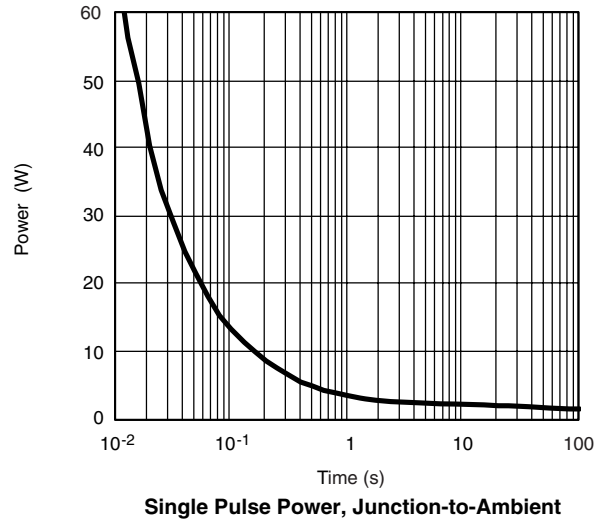
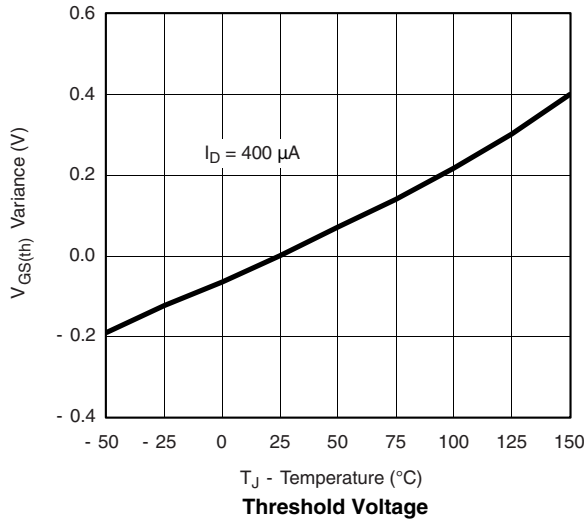


Source-Drain Diode Forward Voltage



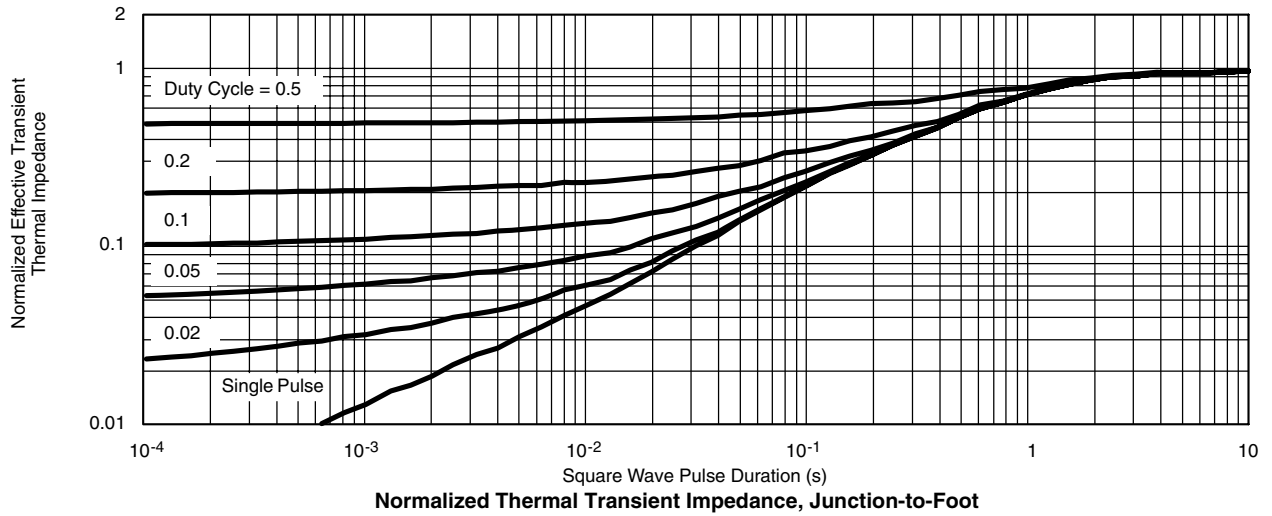
On-Resistance vs. Gate-to-Source Voltage

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted





TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



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